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## **Contents**

|          | METROLOGY KEYNOTE SESSION  |
|----------|--|
| 11611 07 | The emergence of inline screening for high volume manufacturing (Keynote Paper) [11611-2]  |
|          | OVERLAY ACCURACY I   |
| 11611 OB | High voltage scanning electron microscope overlay metrology accuracy for after development inspection [11611-6]                        |
| 11611 OC | Characterization of metrology to device overlay offset and novel methods to minimize it [11611-7]                                      |
| 11611 OE | Machine learning for Tool Induced Shift (TIS) reduction: an HVM case study [11611-117]   |
|          | CHALLENGES AND NEW METHODS   |
| 11611 0G | Microsphere-assisted ultra-small spot spectral reflectometry technique for semiconductor device metrology [11611-10]                   |
| 11611 OH | High-speed wafer film measurement with heterogeneous optical sensor system [11611-11]  |
| 11611 01 | Metrology of thin layer deposition with combined XRR-GIXRF analysis at SOLEIL synchotron [11611-12]                                    |
| 11611 OJ | An innovative probe microscopy solution for measuring conductivity profiles in 3-dimensions [11611-13]                                 |
| 11611 OK | Scanning microwave impedance microscopy for materials metrology [11611-14]   |
|          | INSPECTION   |
| 11611 OL | A new metrology technique for defect inspection via coherent Fourier scatterometry using orbital angular momentum beams [11611-16]     |
| 11611 OM | In-line schematic failure analysis technique by defect SEM images [11611-17]   |
| 11611 ON | e-Beam detection of over-etch in semiconductor processing and how over-etch level is related to defect detection parameters [11611-18] |

| 11611 00 | Frequency encoding scheme for reticle front and back side inspection [11611-19]   |
|----------|---|
| 11611 OP | Defect simulation in SEM images using generative adversarial networks [11611-20]  |
|          |   |
|          | X-RAY AND HIGH ASPECT RATIO METROLOGY   |
| 11611 OS | High resolution profiles of 3D NAND pillars using x-ray scattering metrology [11611-23]   |
| 11611 OT | Comparative near infrared through-focus scanning optical microscopy for 3D memory subsurface defect detection and classification [11611-24]         |
| 11611 OU | Measurability analysis of the HAR structure in 3D memory by T-SAXS simulation [11611-25]  |
| 11611 OV | Fast in-device overlay metrology on multi-tier 3DNAND devices without DECAP and its applications in process characterization and control [11611-26] |
| 11611 OW | X-ray critical dimension metrology solution for high aspect ratio semiconductor structures [11611-27]   |
| 11611 OX | Evaluation of deep learning model for 3D profiling of HAR features using high-voltage CD-SEM [11611-119]  |
|          | CONTOUR METROLOGY   |
| 11611 OY | Investigating SEM-contour to CD-SEM matching (Invited Paper) [11611-28]   |
| 11611 OZ | Pattern placement and shape distortion control using contour-based metrology [11611-29]   |
| 11611 10 | Roughness measurement of 2D curvilinear patterns: challenges and advanced methodology [11611-30]  |
| 11611 11 | Massive metrology and inspection solution for EUV by area inspection SEM with machine learning technology [11611-31]                                |
| 11611 12 | Better prediction on patterning failure mode with hotspot aware OPC modeling [11611-32]   |
| 11611 13 | Contour-based process characterization, modeling, and control for semiconductor manufacturing [11611-118]   |
|          | ROUGHNESS METROLOGY   |
| 11611 15 | SEM image denoising with unsupervised machine learning for better defect inspection and metrology [11611-33]  |

| 11611 17                         | Evaluating SEM-based LER metrology using a metrological tilting-AFM [11611-35]   |
|----------------------------------|--|
| 11611 18                         | Determining the validity domain of roughness measurements as a function of CD-SEM acquisition conditions [11611-36]  |
| 11611 1A                         | Denoising sample-limited SEM images without clean data [11611-38]  |
| 11611 1B                         | Diagnosing and removing CD-SEM metrology artifacts [11611-39]  |
|                                  |  |
|                                  | PROCESS CONTROL  |
| 11611 1E                         | Optimizing focus and dose process windows for robust process control using a multi-feature analysis [11611-41]   |
| 11611 1F                         | Privacy preserving amalgamated machine learning for process control [11611-42]   |
| 11611 1G                         | Hybrid overlay control solution with CDSEM and optical metrology [11611-43]  |
| 11611 11                         | Novel methods for stitching and overlay corrections [11611-45]   |
|                                  |  |
|                                  |  |
|                                  | SCATTEROMETRY  |
| 11611 1J                         | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]   |
| 11611 1J<br>11611 1M             | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference   |
|                                  | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet  |
| 11611 1M                         | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet (Karel Urbanek Best Student Paper Award) [11611-50]  Unsupervised density-based machine learning for abnormal leveling signatures detection  |
| 11611 1M<br>11611 1N             | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet (Karel Urbanek Best Student Paper Award) [11611-50]  Unsupervised density-based machine learning for abnormal leveling signatures detection [11611-51]  Ellipsometric critical dimension metrology employing mid-infrared wavelengths for high-  |
| 11611 1M<br>11611 1N<br>11611 1O | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet (Karel Urbanek Best Student Paper Award) [11611-50]  Unsupervised density-based machine learning for abnormal leveling signatures detection [11611-51]  Ellipsometric critical dimension metrology employing mid-infrared wavelengths for high-aspect-ratio channel hole module etch processes [11611-52]  Methods to overcome limited labeled data sets in machine learning-based optical critical                                |
| 11611 1M<br>11611 1N<br>11611 1O | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet (Karel Urbanek Best Student Paper Award) [11611-50]  Unsupervised density-based machine learning for abnormal leveling signatures detection [11611-51]  Ellipsometric critical dimension metrology employing mid-infrared wavelengths for high-aspect-ratio channel hole module etch processes [11611-52]  Methods to overcome limited labeled data sets in machine learning-based optical critical                                |
| 11611 1M<br>11611 1N<br>11611 1O | A breakthrough on throughput and accuracy limitation in ellipsometry using self-interference holographic analysis [11611-46]  Latent image characterization by spectroscopic reflectometry in the extreme ultraviolet (Karel Urbanek Best Student Paper Award) [11611-50]  Unsupervised density-based machine learning for abnormal leveling signatures detection [11611-51]  Ellipsometric critical dimension metrology employing mid-infrared wavelengths for high-aspect-ratio channel hole module etch processes [11611-52]  Methods to overcome limited labeled data sets in machine learning-based optical critical dimension metrology [11611-53] |

| 11611 1T | In-line Raman spectroscopy for stacked nanosheet device manufacturing [11611-57]  |
|----------|---|
| 11611 1U | OCD enhanced: implementation and validation of spectral interferometry for nanosheet inner spacer indentation [11611-58]                                    |
|          | EDGE PLACEMENT ERROR  |
| 11611 IV | Edge placement error wafer mapping and investigation for improvement in advanced DRAM node [11611-59]   |
| 11611 1W | Improvement of EPE measurement accuracy on ADI wafer, the method of using machine learning trained with CAD [11611-60]                                      |
| 11611 1Y | Contour-based metrology for assessment of edge placement error and its decomposition into global/local CD uniformity and LELE intralayer overlay [11611-62] |
|          | OVERLAY ACCURACY II   |
| 11611 22 | Self-referenced and self-calibrated MoiréOVL target design and applications [11611-66]  |
| 11611 23 | Statistical process optimization method for metrology equipment [11611-67]  |
| 11611 24 | Signal weighted overlay optimizer for scatterometry metrology [11611-69]  |
| 11611 25 | Moiré effect-based overlay target design for OPO improvements [11611-70]  |
| 11611 26 | Novel diffraction-based overlay metrology utilizing phase-based overlay for improved robustness [11611-71]  |
|          | METROLOGY AND INSPECTION FOR THE EUV ERA  |
| 11611 27 | The unavoidable renaissance of electron metrology in the age of high NA EUV (Invited Paper) [11611-72]  |
| 11611 28 | Defect characterization of 28 nm pitch EUV single patterning structures for iN5 node [11611-73]   |
| 11611 29 | Massive e-beam metrology and inspection for analysis of EUV stochastic defect [11611-74]  |
| 11611 2A | Scatterometry solutions for 14nm half-pitch BEOL layers patterned by EUV single exposure [11611-75]   |
| 11611 2B | Assessment of stochastic fail rate using E-beam massive metrology [11611-76]  |

11611 2C Multivariate analysis methodology for the study of massive multidimensional SEM data [11611-77] **LATE BREAKING** 11611 2D Virtual metrology: how to build the bridge between the different data sources [11611-78] 11611 2E Recent advancements in atomic force microscopy [11611-121] **POSTER SESSION** 11611 2F Broadband scatterometry at extreme ultraviolet wavelengths for nanograting characterization [11611-49] 11611 2G Detection and correlation of yield loss induced by color resist deposition deviation with a deep learning approach applied to optical acquisitions [11611-79] 11611 2H Defect characterization of EUV Self-Aligned Litho-Etch Litho-Etch (SALELE) patterning scheme for advanced nodes [11611-80] 11611 21 Effects of lithography process conditions on unbiased line roughness by PSD analysis [11611-81] 11611 2J Mark design challenge of cut layer in FinFet [11611-82] 11611 2L Data fusion by artificial neural network for hybrid metrology development [11611-84] 11611 2M Imaging-based overlay metrology optimized by HV-SEM in 3D-NAND process [11611-85] Study of high throughput EUV mask pattern defect inspection technologies using multibeam 11611 2N electron optics [11611-86] 11611 20 Accuracy enhancement in imaging-based overlay metrology by optimizing measurement conditions per layer [11611-87] 11611 2P Process variation impacts on optical overlay accuracy signature [11611-88] 11611 2Q Non-destructive depth measurement using SEM signal intensity [11611-89] 11611 2S Absolute coordinate system adjustment and calibration by using standalone alignment metrology system [11611-91] 11611 2U An accurate and robust after-develop overlay measurement solution using YieldStar multiwavelength optical metrology accompanied by a precise application strategy [11611-93] 11611 2V Introducing machine learning-based application for writer main pole CD metrology by dual

**beam FIB/SEM** [11611-95]

| 11611 2W | A novel method of overlay variation study for 3D NAND channel hole [11611-97]   |
|----------|---|
| 11611 2X | AFM line space trench and depth measurement of fan-out fine-pitch high aspect ratio redistribution layer structure [11611-99]                 |
| 11611 2Z | Accuracy aware pixel selection in multi-wavelength µDBO metrology enables higher robustness and accuracy for DRAM [11611-102]                 |
| 11611 31 | Method to improve the overlay image contrast and optimize the sub-segmentation mark [11611-104]   |
| 11611 32 | Excursion detection and root-cause analysis using virtual overlay metrology [11611-105]   |
| 11611 33 | Robustness improvement in imaging-based overlay metrology for high topography layers by Talbot targets [11611-106]                            |
| 11611 34 | Lithography PR profile improvement and defects reduction by film pre-treatment [11611-107]  |
| 11611 35 | Automated extraction of critical dimension from SEM images with Weave <sup>TM</sup> [11611-108]   |
| 11611 36 | In-line applications of atomic force microscope based topography inspection for emerging roll-to-roll nanomanufacturing processes [11611-109] |
| 11611 39 | Investigation and optimization of STI dry-etch induced overlay through patterned wafer geometry tool [11611-113]                              |
| 11611 3A | Plasma assisted particle contamination control: plasma charging dependence on particle morphology [11611-114]                                 |
| 11611 3B | A study on diffraction-based overlay measurement based on FDTD method [11611-116]   |